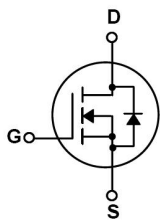


TO-262 N MOS

N-CHANNEL MOSFET in a TO-262 Plastic Package.

Low gate charge, low crss, fast switching, HF product.

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



PIN1 G

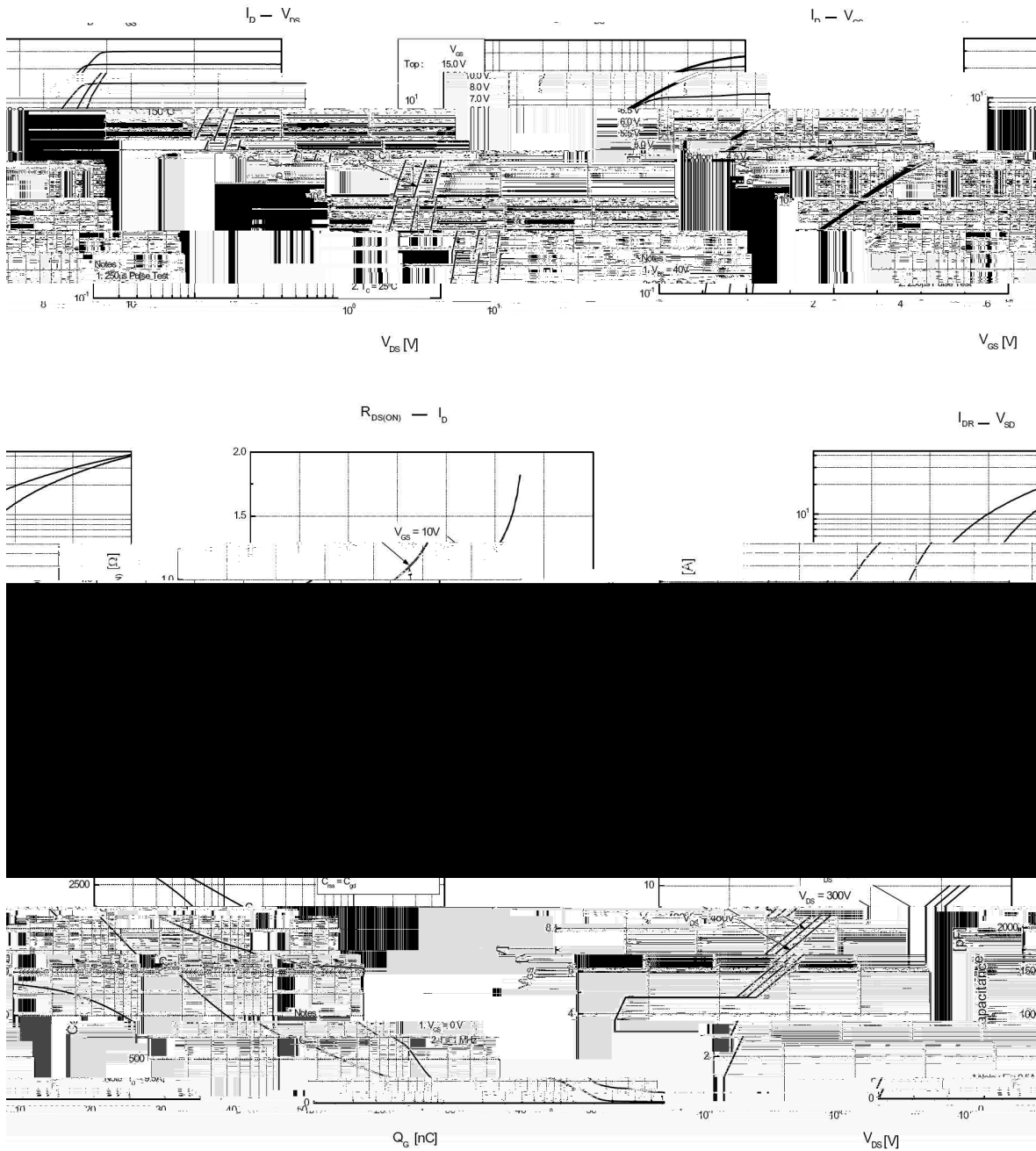
PIN 2 D

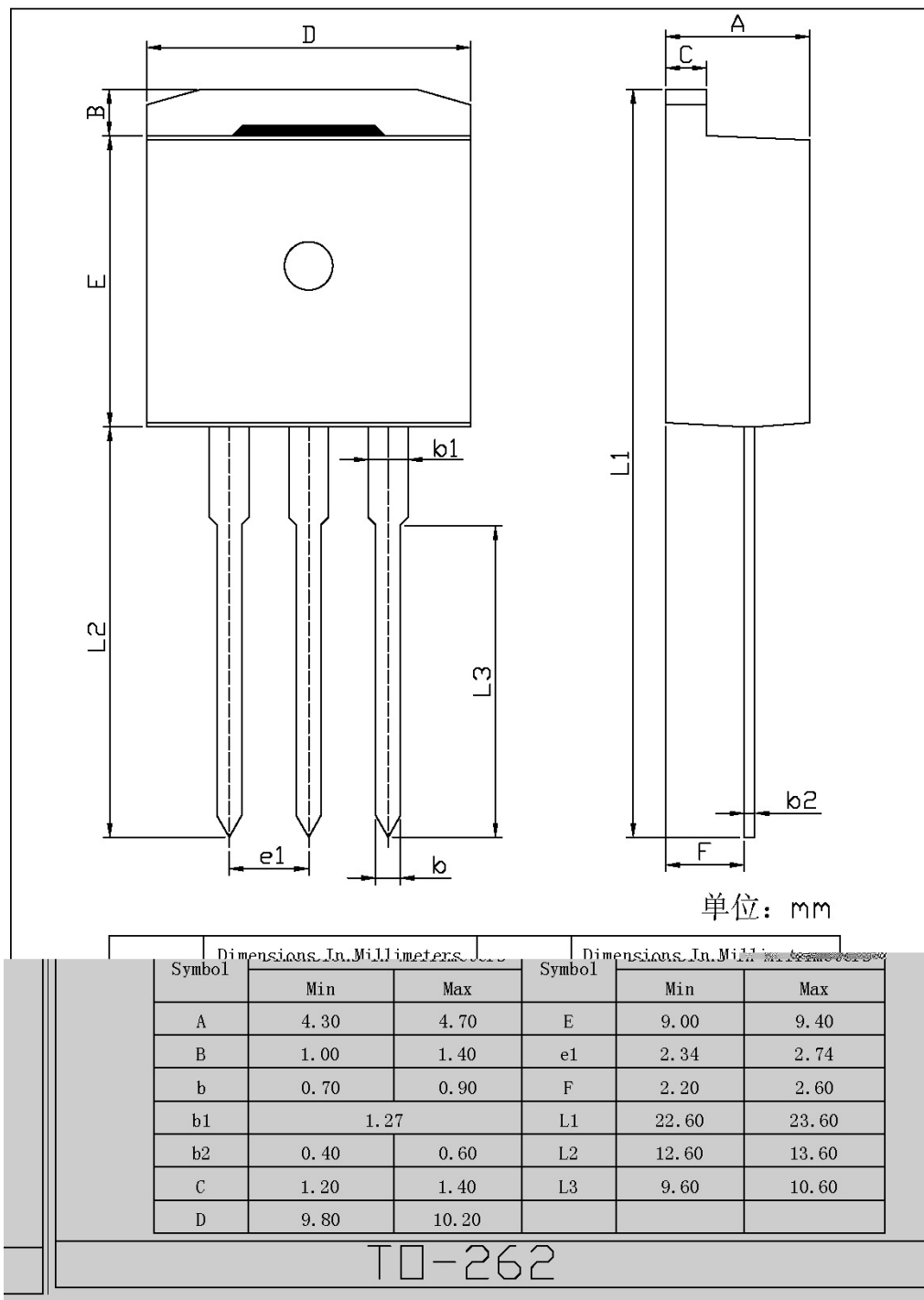
PIN 3 S

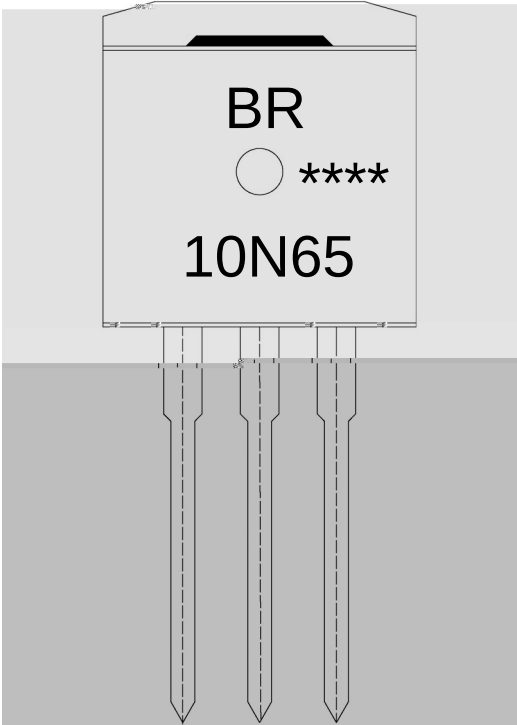
See Marking Instructions

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	10	A
Drain Current	$I_D(T_c=100^\circ\text{C})$	5.7	A
Drain Current - Pulsed	I_{DM}	38	A
Gate-Source Voltage	V_{GS}	± 20	V
Single Pulsed Avalanche Energy	E_{AS}	488.9	mJ
Avalanche Current	I_{AR}	9.5	A
Thermal Resistance, Junction-to-Case	R_{JC}	0.8	/W
Thermal Resistance, Junction-to-Ambient	R_{JA}	65	/W
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	156	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\text{ A}$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}				



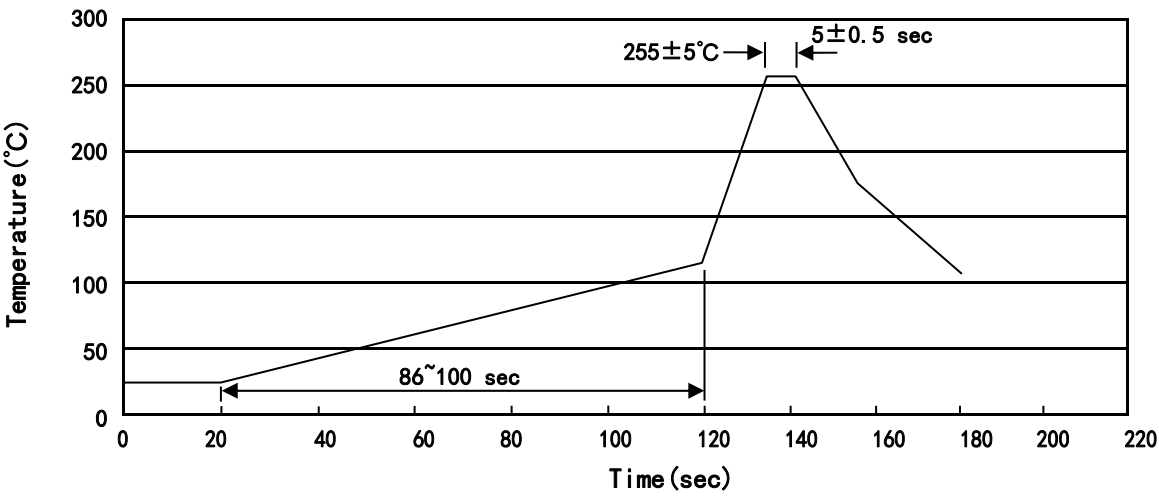




10N65

Note:

- | | |
|--------|--|
| BR: | Company Code |
| 10N65: | Product Type Code |
| ****: | Lot No. Code, code change with Lot No. |



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-262	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

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